

PRODUCT CHARACTERISTICS

V_{DSS}	60V
$R_{DS(ON) Typ(@V_{GS}=10V)}$	2.3m Ω
$R_{DS(ON) Typ(@V_{GS}=4.5V)}$	3m Ω
I_D	154A

APPLICATIONS

- * Electronic lamp ballasts based on half bridge
- * Load Switching, Quick/Wireless Charge.
- * Motor Driving

FEATURE

- * Low Gate Charge
- * Pb-Free Lead Plating



ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT6127T	TOLL	2000 pieces/Reel

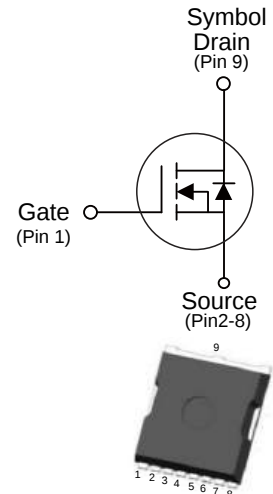
ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current Continuous($@V_{GS}=10V, T_A=25^{\circ}C$)	I_D	154	A
Drain Current Continuous($@V_{GS}=10V, T_A=100^{\circ}C$)	I_D	109	A
Drain Current Pulsed	I_{DM}	616	A
Avalanche Energy *	E_{AS}	484	mJ
Power Dissipation	P_D	120	W
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	1.04	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$



TOLL

■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V,I _D =250μA	60	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{GS} =+20V,V _{DS} =0V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{GS} =-20V ,V _{DS} =0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =20 A	-	2.3	3	mΩ
		V _{GS} =4.5V,I _D =15 A	-	3	4	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.83	2.5	V
Dynamic characteristics						
Gate Resistance	R _g	V _{GS} =0V,V _{DS} =0V ,f=1.0MHz	-	1.3	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V,I _D =5A	-	33	-	S
Input Capacitance	C _{iss}	V _{DS} =30V,V _{GS} =0V f=1.0MHz	-	3800	-	pF
Output Capacitance	C _{oss}		-	730	-	pF
Reverse Transfer Capacitance	C _{rss}		-	35	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =30V, I _D =75A ,R _G =1.5Ω	-	11	-	ns
Rise Time	t _r		-	28	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	54	-	ns
Fall Time	t _f		-	30	-	ns
Total Gate Charge	Q _g	I _D =75A, V _{DS} =30V V _{GS} =10V	-	62	-	nC
Gate to Source Charge	Q _{gs}		-	10	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	14	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	154	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	616	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.69	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =75A, T _J =25 °C dI/dt=100A/μs	-	57	-	ns
Reverse Recovery Charge	Q _{rr}		-	69	-	nC

■ TYPICAL CHARACTERISTICS

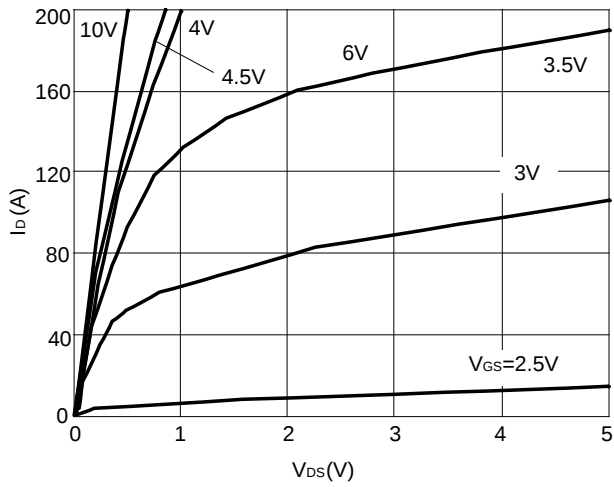


Figure 1: Output Characteristics

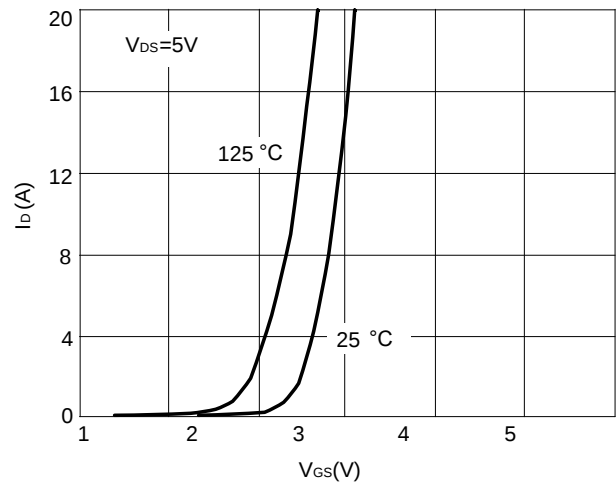


Figure 2: Typical Transfer Characteristics

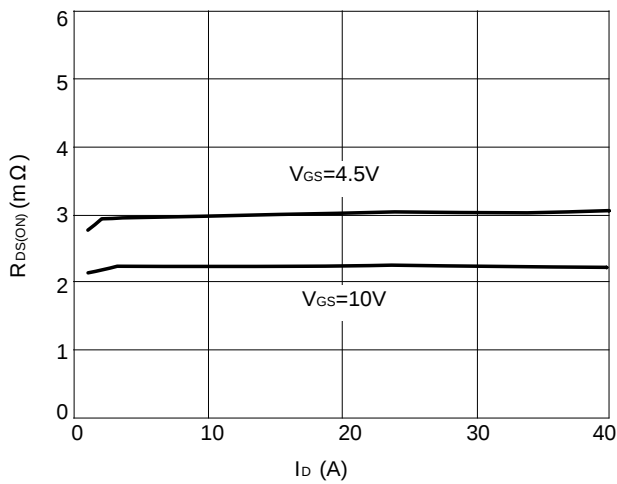


Figure 3: On-Resistance vs. Drain Current

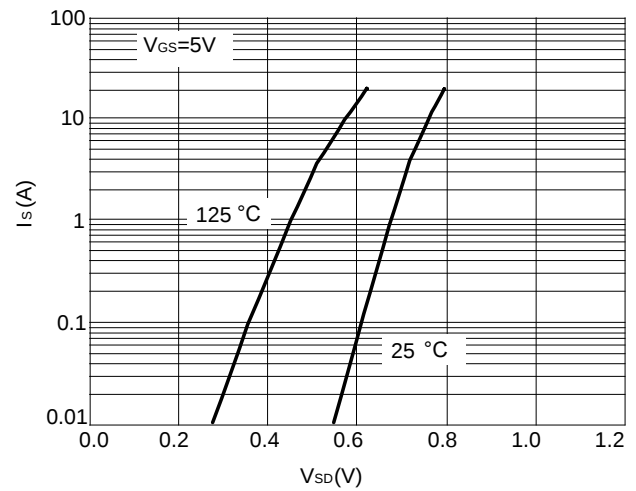


Figure 4: Body Diode Characteristics

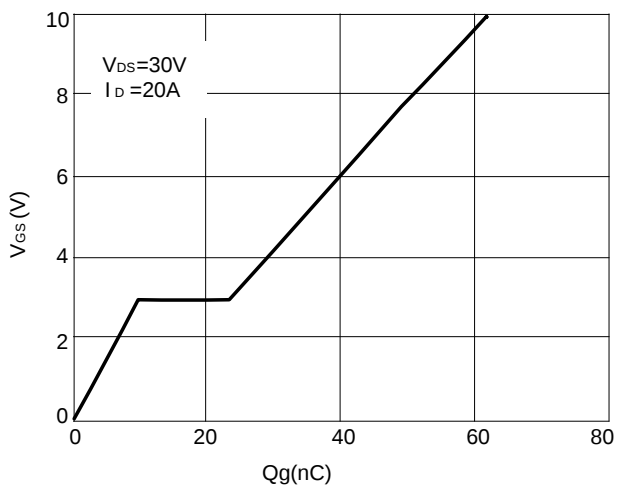


Figure 5: Gate Charge Characteristics

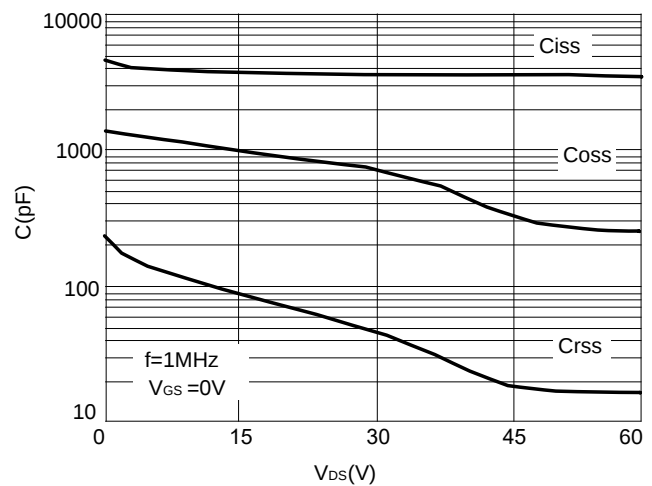


Figure 6: Capacitance Characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

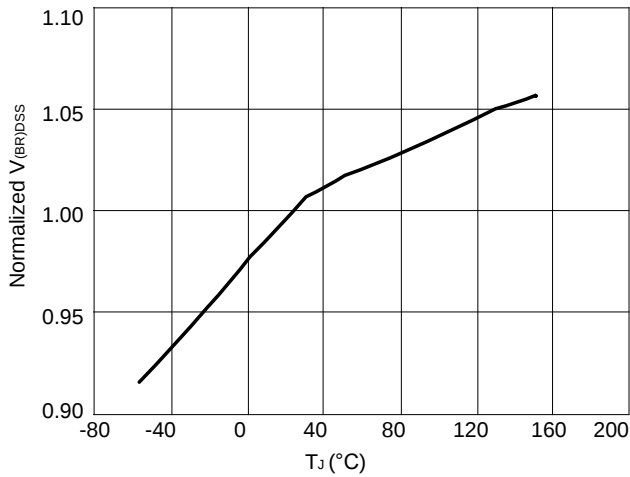


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

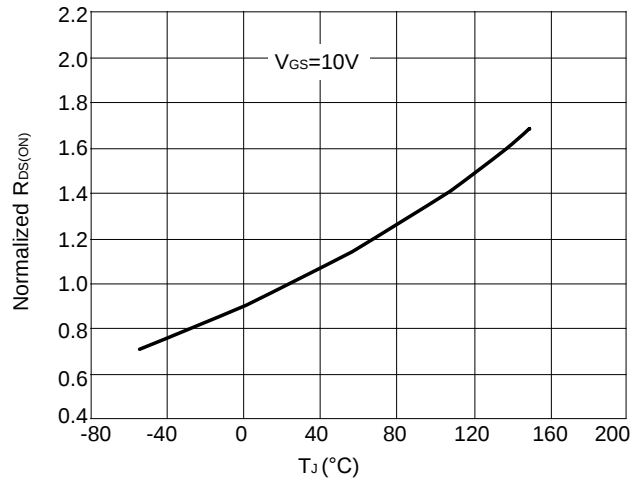


Figure 8: Normalized on-Resistance vs. Junction Temperature

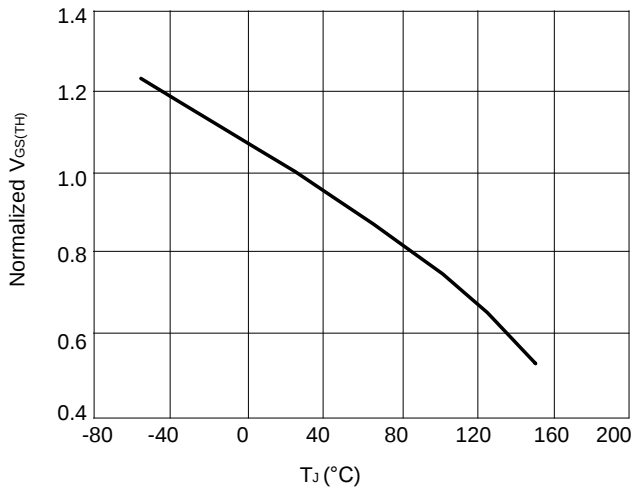


Figure 9: Normalized Threshold Voltage vs. Junction Temperature

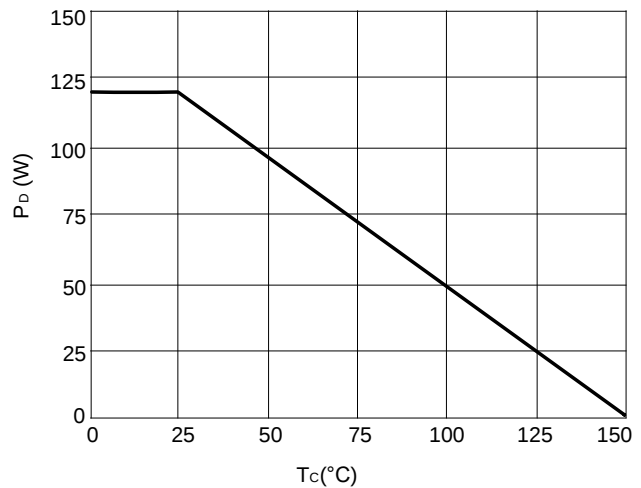


Figure 10: Power De-rating

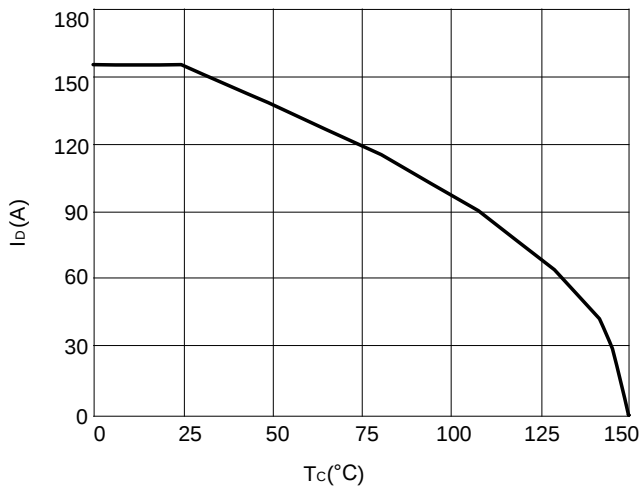


Figure 11: Current De-rating

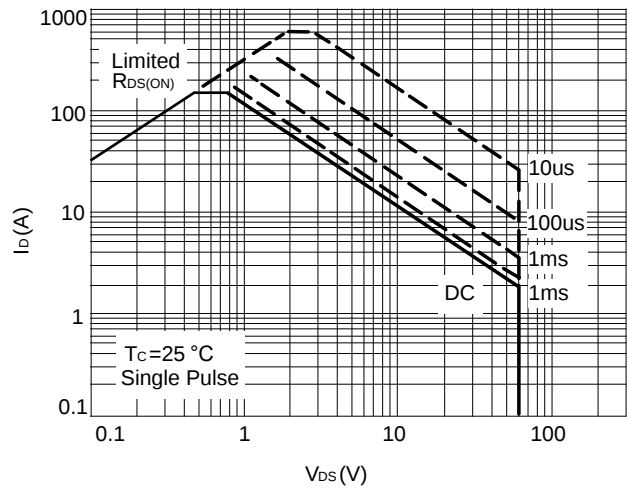
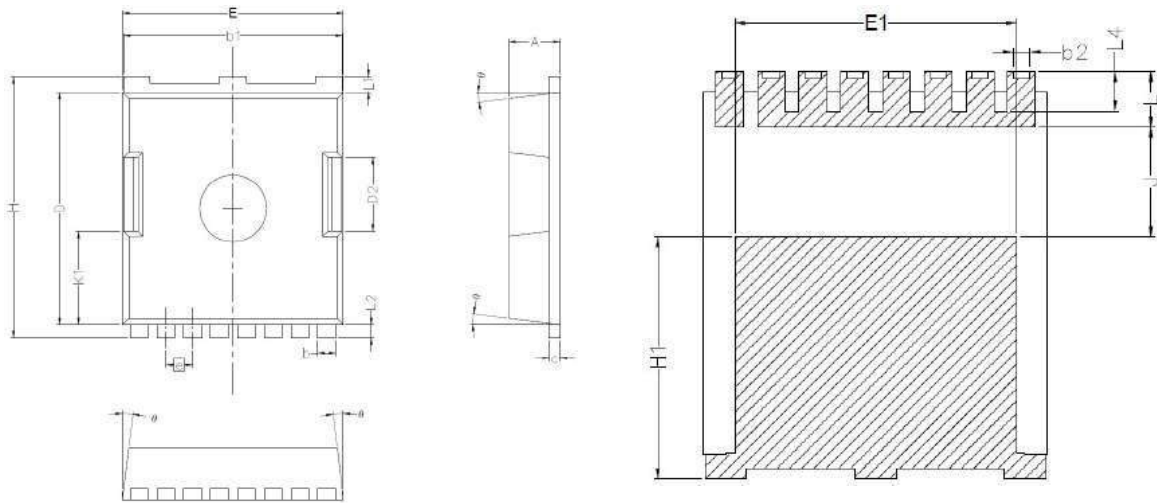


Figure 12: Maximum Safe Operating Area

■ TOLL PACKAGE OUTLINE DIMENSIONS



Symbol	Dimesions In Millimeters	
	Min.	Max.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4.	10°